MGBR5L100 Preliminary DIODE

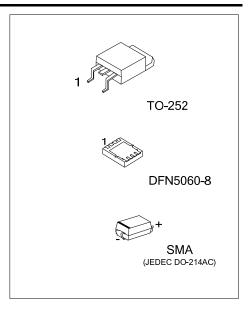
MOS GATED BARRIER RECTIFIER

■ DESCRIPTION

The UTC MGBR5L100 is a surface mount mos gated barrier rectifier, it uses UTC's advanced technology to provide customers withlow forward voltage drop and high switching speed, etc.

■ FEATURES

- * Low forward voltage drop
- * High switching speed



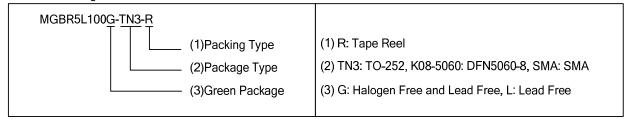
■ SYMBOL

SMA	TO-252	DFN5060-8				
2 — 1 K	1. A ° 2. K	1. A				

■ ORDERING INFORMATION

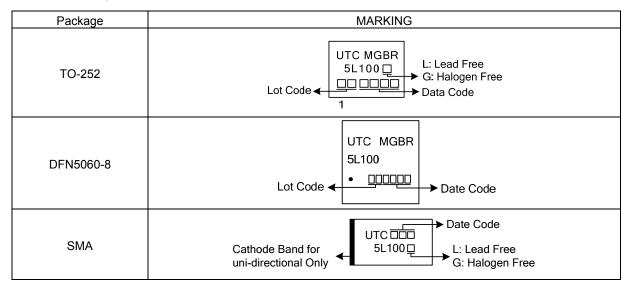
Ordering Number		Daakaga	Pin Assignment							Dooking	
Lead Free	Halogen Free	Package	1	2	3	4	5	6	7	8	Packing
MGBR5L100L-TN3-R	GBR5L100L-TN3-R MGBR5L100G-TN3-R		Α	Κ	Α	-	1	-	-	ı	Tape Reel
MGBR5L100L-K08-5060-R	MGBR5L100G-K08-5060-R	DFN5060-8	Α	Α	Α	NC	Κ	Κ	Κ	Κ	Tape Reel
MGBR5L100L-SMA-R	MGBR5L100G-SMA-R	SMA	K	Α	-	-	-	-	-	-	Tape Reel

Note: Pin Assignment: A: Anode K: Cathode



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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER	SYMBOL	RATINGS	UNIT
DC Blocking Voltage	V_{RM}	100	V
Working Peak Reverse Voltage	V_{RWM}	100	V
Repetitive Peak Reverse Voltage	V_{RRM}	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	V
Average Rectified Output Current T _C =80°C	l _o	5	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Lo	l=a	100	Α
Operating Junction Temperature	TJ	-65 ~ +150	°C
Storage Temperature	T _{STG}	-65 ~ + 150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA (Note 3)

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-252		32	
	DFN5060-8	θЈΑ	72	°C/W
	SMA		75	
Junction to Case	TO-252		2.5	
	DFN5060-8	θυς	2.4	°C/W
	SMA		35	

■ **ELECTRICAL CHARACTERISTICS**(T_A=25°C,unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I _R =0.5mA	100			V
Forward Voltage Drop	VEM	I _F =5A, T _J =25°C			0.80	V
		I _F =5A, T _J =125°C			0.75	V
Leakage Current (Note 1)	DM	V _R =100V, T _J =25°C			250	μA
		V _R =100V, T _J =125°C			25	mA

Notes: 1. Short duration pulse test used to minimize self-heating effect.

- 2. Thermal resistance junction to case mounted on heatsink.
- 3. Mounted on an FR4 PCB, single-sided copper, with 100 cm² copper pad area.

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